

# Thermal Model of EPC2619



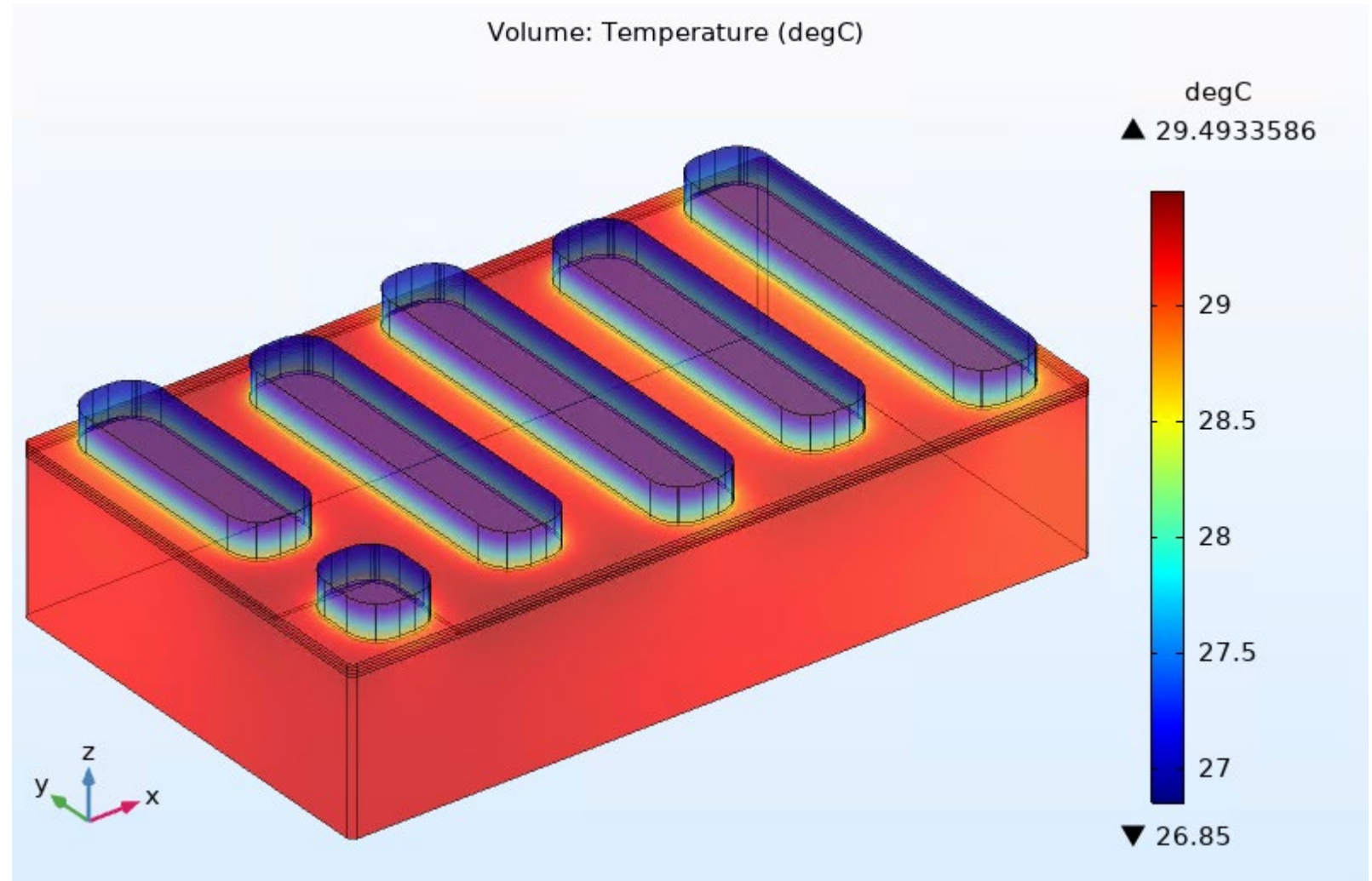
# EPC2619 FEA thermal simulation



- The thermal model applies to EPC2619.
- A power dissipation of 1 W in the device active area is assumed.
- Finite element analysis (FEA) thermal simulations
  - $R_{\Theta JB}$  and  $R_{\Theta JC}$  are obtained by stationary simulations.
  - $Z_{\Theta JB}$  and  $Z_{\Theta JC}$  are obtained by transient simulations.
- R-C thermal model is generated.

# Steady-state $R_{\Theta JB}$

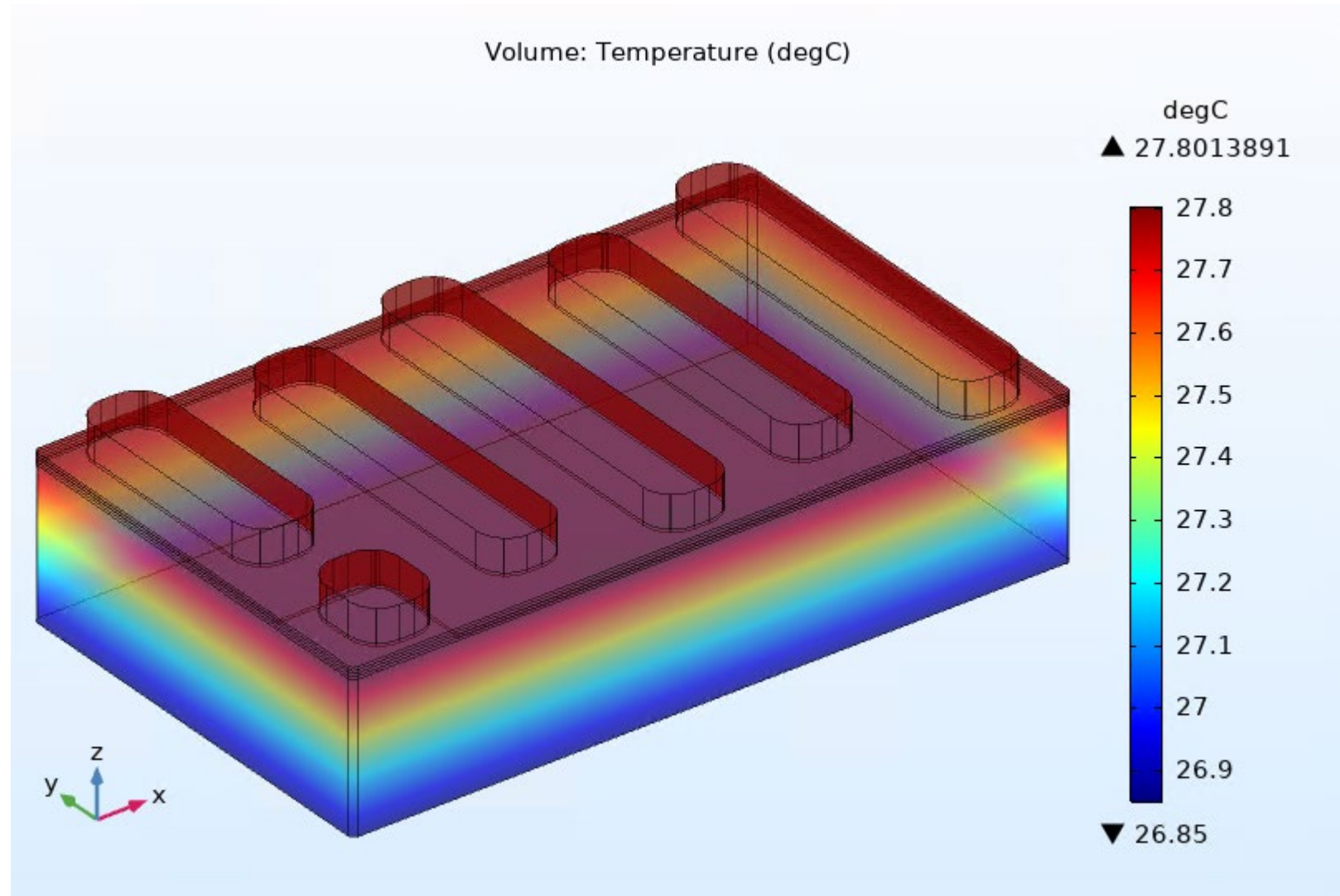
- Example:  $P = 1 \text{ W}$





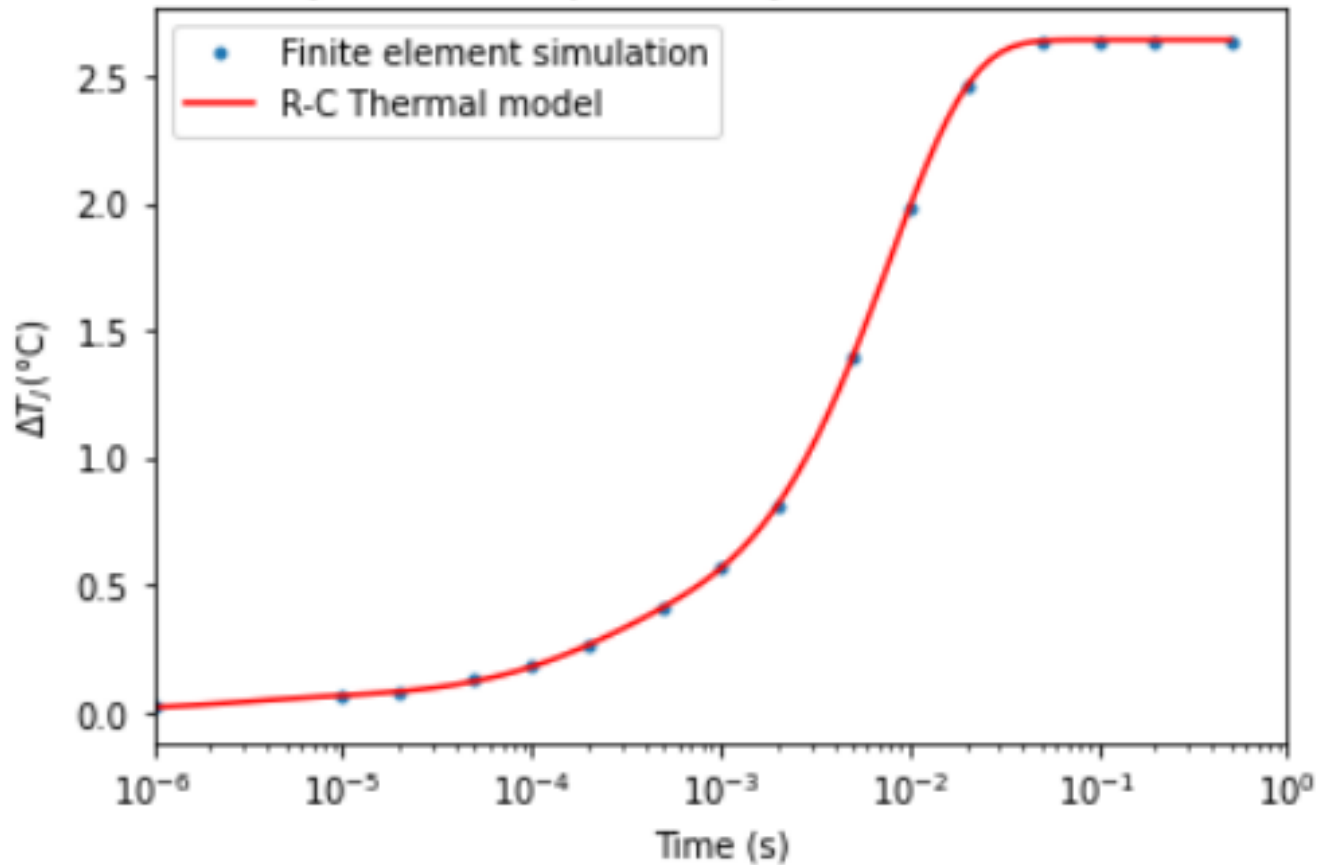
# Steady-state $R_{\Theta Jc}$

- Example:  $P = 1 \text{ W}$

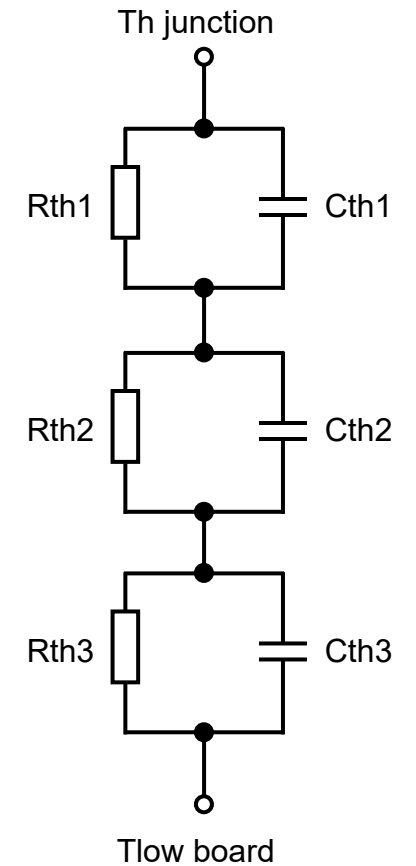


# $Z_{\Theta JB}$ R-C thermal model

Transient junction temperature (Junction to Board, P = 1 W)

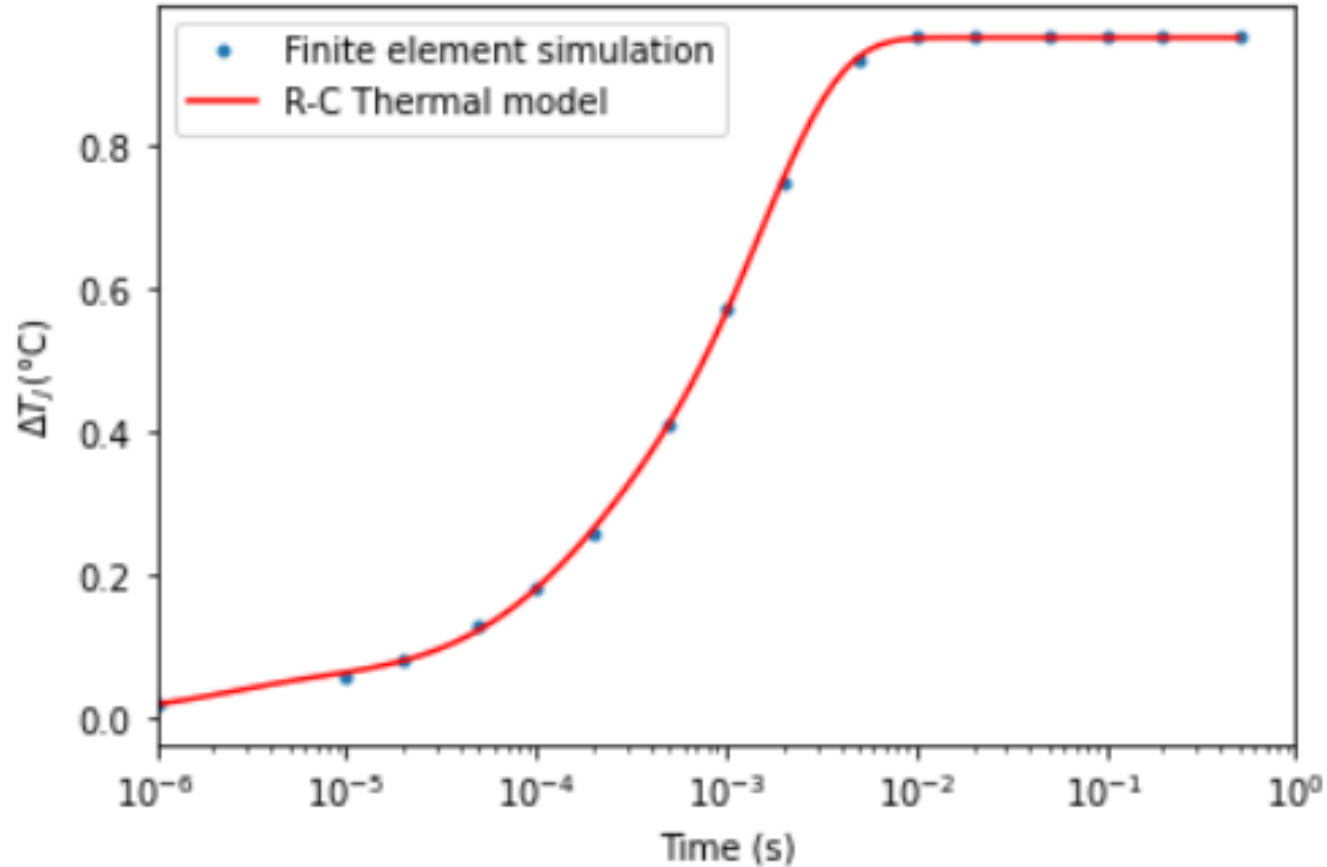


Model Parameter	Value	Unit
Rth1	5.14E-02	°C/W
Rth2	2.31E-01	
Rth3	2.36E+00	
Cth1	4.91E-05	J/°C
Cth2	7.94E-04	
Cth3	3.33E-03	

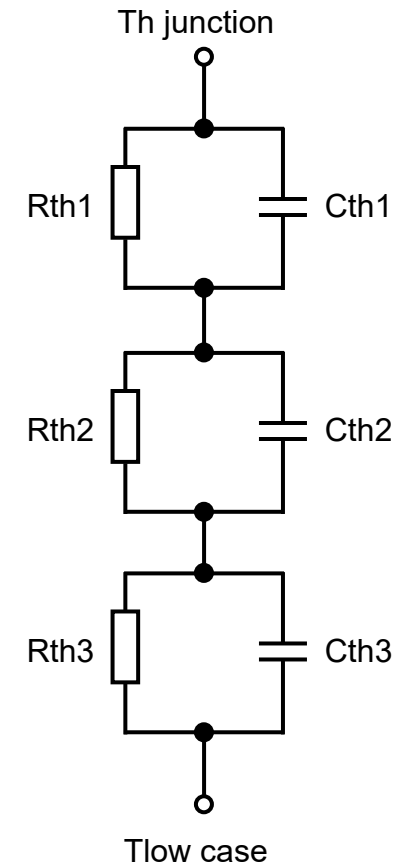


# $Z_{\Theta JC}$ R-C thermal model

Transient junction temperature (Junction to Case, P = 1 W)



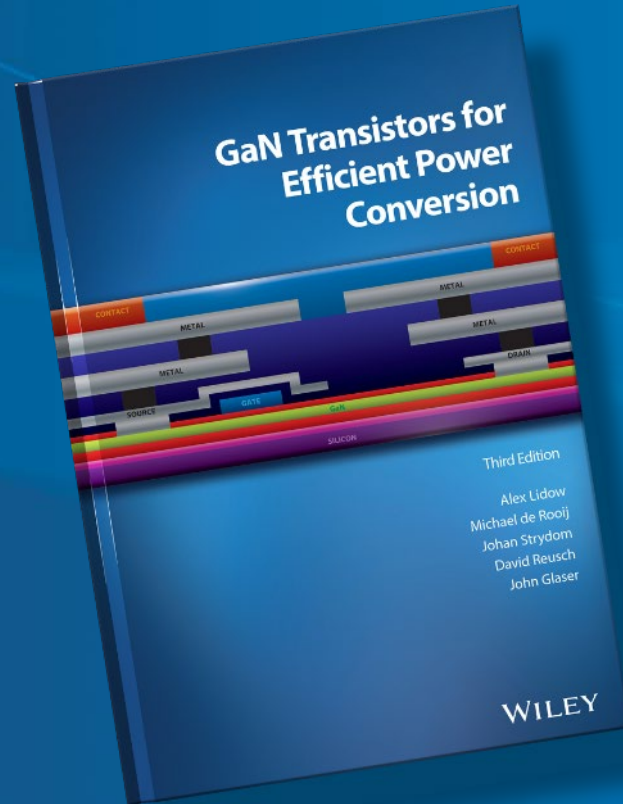
Model Parameter	Value	Unit
Rth1	4.75E-02	°C/W
Rth2	1.54E-01	
Rth3	7.48E-01	
Cth1	4.53E-05	J/°C
Cth2	8.09E-04	
Cth3	2.01E-03	



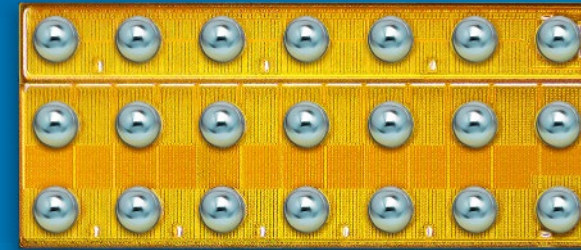


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